AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims

1. (Currently Amended) A semiconductor fabricating device, comprising:

an adhesion unit installed on a base body in a production line, the adhesion unit having an adhesion chamber that supplies an adhesion enhancing material that reinforces adhesion between a wafer and a photoresist layer when the photoresist layer is deposited on the wafer and that generates a process deteriorating gas; ~~and~~

a cooling unit installed in the production line to cool down the wafer transferred from the adhesion unit; and

a bake unit installed in the production line, the bake unit being adapted to bake the wafer having the photoresist layer formed thereon, the baking being susceptible to operational failures if exposed to the process deteriorating gas,

wherein the bake unit and the cooling unit are ~~is~~ installed at a higher level than the adhesion unit, and

wherein clean air flows downward over the adhesion, cooling, and bake units to carry the process deteriorating gas away from the bake unit and cooling unit.

2. (Canceled).

3. (Original). The semiconductor fabricating device of claim 1, wherein the process deteriorating gas is ammonia (NH_4).

4. (Currently Amended). A semiconductor fabricating device, comprising:

an adhesion unit installed on a base body in a production line, the adhesion unit having an adhesion chamber that supplies an adhesion enhancing material that reinforces adhesion between a wafer and a photoresist layer when the photoresist layer is deposited on the wafer and that generates a process deteriorating gas; ~~and~~

a cooling unit installed in the production line to cool down the wafer transferred from the adhesion unit; and

a bake unit installed in the production line, the bake unit being adapted to bake the wafer having the photoresist layer formed thereon, the baking being susceptible to operational failures if exposed to the process deteriorating gas,

wherein the adhesion unit is installed at a first position, ~~and~~ the bake unit is installed at a second position, and the cooling unit is installed at a third position, and

wherein clean air flows from the second and third positions ~~position~~ where the bake unit and cooling unit are ~~is~~ installed to the first position where the adhesion unit is installed, to carry the process deteriorating gas away from the bake unit and the cooling unit.

5. (Canceled).

6. (Previously Presented). The semiconductor fabricating device of claim 4, wherein the processing deteriorating gas is ammonia (NH_4).

7. (Currently Amended). The semiconductor fabricating device of claim 4, wherein the second and third positions are ~~position is~~ at a higher location within the semiconductor fabricating device than the first position.

8. (Currently Amended). A method of fabricating a semiconductor device comprising:

performing first semiconductor fabricating processes at a first location installed on a base body in a production line, the first semiconductor fabricating processes generating a process deteriorating gas;

performing second semiconductor fabricating processes that are dependent on the first semiconductor fabricating processes at a second location and a third location, the second semiconductor fabricating processes being susceptible to operational failures upon exposure to the process deteriorating gas; and

flowing clean air from the second location and the third location to the first location to carry the process deteriorating gas away from the second location and the third location,

wherein the first semiconductor fabricating processes include supplying an adhesion enhancing material that reinforces adhesion between a wafer and a photoresist layer when the photoresist layer is deposited onto the wafer, and

wherein the second semiconductor fabricating processes include baking and cooling down the wafer having the photoresist layer thereon.

9. (Canceled)

10. (Original). The method of fabricating a semiconductor device of claim 8, wherein the process deteriorating gas is ammonia (NH_4).

11. (Original). The method of fabricating a semiconductor device of claim 8, wherein the second location is higher than the first location.

12. (Original). The method of fabricating a semiconductor device of claim 8, wherein the second semiconductor fabricating processes are performed after the first semiconductor fabricating processes.

13. (Currently Amended). A semiconductor fabricating device, comprising:

a first semiconductor process unit installed in a production line that performs first semiconductor fabricating processes and that generates a process deteriorating gas during the first semiconductor fabricating process; and

second semiconductor process units installed in the production line that perform second semiconductor fabricating processes dependent on the first semiconductor fabricating processes, the second semiconductor fabricating processes being susceptible to operational failures if exposed to the process deteriorating gas,

wherein the first semiconductor process unit is an adhesion unit,

wherein the second semiconductor process units comprise bake and cooling units, and

wherein all of the second semiconductor process units are installed so that clean air flows over the first and second semiconductor process units to carry the process deteriorating gas away from the second semiconductor process units.

14. (Previously Presented). The semiconductor fabricating device of claim 13, wherein all the second semiconductor process units are installed at a higher level than the adhesion unit when clean air flows downward over the first and second semiconductor process units to carry the process deteriorating gas away from the second semiconductor process units.

15. (Previously Presented). The semiconductor fabricating device of claim 13, wherein all the second semiconductor process units are installed at a lower level than the adhesion unit when clean air flows upward over the first and second semiconductor process units to carry the process deteriorating gas away from the second semiconductor process units.

16. (Previously Presented). The semiconductor fabricating device of claim 13, wherein the second semiconductor process units comprise process units being susceptible to operational failures if exposed to the process deteriorating gas.

17. (Previously Presented). The semiconductor fabricating device of claim 13, wherein the second semiconductor process units comprise bake units and cooling units.

18. (Previously Presented). The semiconductor fabricating device of claim 13, wherein the adhesion unit is installed on a base body when clean air flows downward over the adhesion and second semiconductor process units to carry the process deteriorating gas away from the second semiconductor process units.

19. (Previously Presented). The semiconductor fabricating device of claim 13, wherein the adhesion unit is installed on a base body.

20. (Previously Presented) The semiconductor fabricating device of claim 1, further comprising a cooling unit also installed in the production line, the cooling unit being adapted to cool the wafer after it leaves the adhesion unit and before the photoresist layer is deposited on the wafer,

wherein the cooling unit is installed at a higher level than the adhesion unit, and

wherein clean air flows downward over the cooling unit to carry the process deteriorating gas away from the cooling unit

21. (Canceled)